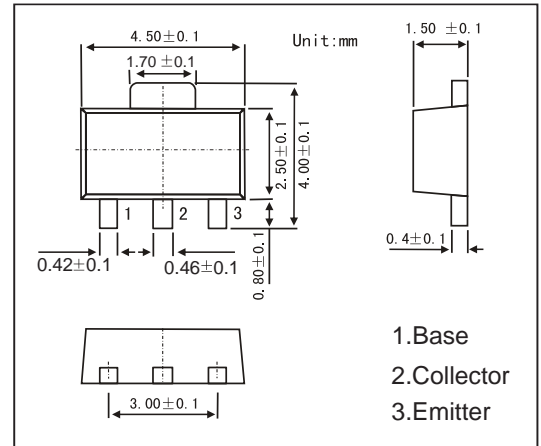


**SOT-89 Plastic-Encapsulate Transistors**
**FEATURES**

- Very small size making it easy to provide high highdensity, small-sized hybrid IC's
- PNP Transistors

**MECHANICAL DATA**

- Case style:SOT-89molded plastic
- Mounting position:any


**MAXIMUM RATINGS AND CHARACTERISTICS**

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CB0</sub>	-25	V
Collector - Emitter Voltage	V <sub>CEO</sub>	-25	
Emitter - Base Voltage	V <sub>EBO</sub>	-5	
Collector Current - Continuous	I <sub>C</sub>	-1	A
Collector current -Pulse	I <sub>CP</sub>	-2	
Collector Power Dissipation (Note.1)	P <sub>C</sub>	0.5	W
		1.3	
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature range	T <sub>stg</sub>	-55 ~ +150	

 Note.1: Mounted on ceramic board (250mm<sup>2</sup> x0.8mm)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> = -100 μA, I <sub>E</sub> =0	-25			V
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -1 mA, R <sub>BE</sub> =∞	-25			
Emitter - base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -100 μ A, I <sub>C</sub> =0	-5			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -20V, I <sub>E</sub> =0			-0.1	uA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -4V, I <sub>C</sub> =0			-0.1	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500 mA, I <sub>B</sub> =-50mA		-0.15	-0.7	V
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-500 mA, I <sub>B</sub> =-50mA		-0.85	-1.2	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> = -50 mA	100		560	
		V <sub>CE</sub> = -2V, I <sub>C</sub> = -1 A	40			
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f = 1MHz		25		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -10V, I <sub>C</sub> = -50mA		180		MHz

## RATINGS AND CHARACTERISTIC CURVES

